

| L Number | Hits  | Search Text  | DB  | Time stamp       |
|----------|-------|--|---|------------------|
| -        | 138   | 257/410.ccls. and (silicide or silicate)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/07 14:56 |
| -        | 35    | 257/410.ccls. and (silicate)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/07 14:56 |
| -        | 231   | 257/411.ccls. and (gate near3 (silicon or silicate or silicide or si))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 08:49 |
| -        | 298   | 257/411.ccls. and (gate or insulator or insulating) near3 (silicon or silicate or silicide or si)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 08:57 |
| -        | 27    | 257/411.ccls. and (gate or insulator or insulating) near3 ((silicon or silicate or silicide or si) and (metal or tungsten or hafnium or zirconium))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 09:01 |
| -        | 110   | 257/411.ccls. and (insulator or insulating or dielectric) near3 (metal or tungsten or hafnium or zirconium)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 10:25 |
| -        | 15694 | gate near3 (dielectric or insulating or insulator or oxide) and (dielectric or insulating or insulator or oxide) near5 (metal near2 oxynitride or metal near2 oxy-nitride or metal near oxide or metal near3 silicate or metal near3 silicide or hafnium near2 oxynitride or zirconium near2 oxynitride or HfSiON or Hf near2 SiON or ZRSiON or Zr near2 SiON)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 10:31 |
| -        | 3851  | gate near3 (dielectric or insulating or insulator or oxide) and (dielectric or insulating or insulator or oxide) near5 (metal near2 oxynitride or metal near2 oxy-nitride or metal near oxide or metal near3 silicate or metal near3 silicide or hafnium near2 oxynitride or zirconium near2 oxynitride or HfSiON or Hf near2 SiON or ZRSiON or Zr near2 SiON) with silicon  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 10:35 |
| -        | 3291  | gate near3 (dielectric or insulating or insulator or oxide) and (dielectric or insulating or insulator or oxide) near5 (metal near2 oxynitride or metal near2 oxy-nitride or metal near oxide or metal near3 silicate or metal near3 silicide or hafnium near2 oxynitride or zirconium near2 oxynitride or HfSiON or Hf near2 SiON or ZRSiON or Zr near2 SiON) with silicon with (metal near oxide)                    | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 10:39 |
| -        | 1493  | 257/\$.ccls. and (gate near3 (dielectric or insulating or insulator or oxide) and (dielectric or insulating or insulator or oxide) near5 (metal near2 oxynitride or metal near2 oxy-nitride or metal near oxide or metal near3 silicate or metal near3 silicide or hafnium near2 oxynitride or zirconium near2 oxynitride or HfSiON or Hf near2 SiON or ZRSiON or Zr near2 SiON) with silicon with (metal near oxide)) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 10:39 |

|   |     |   |   |                  |
|---|-----|---|---|------------------|
| - | 73  | gate near3 (dielectric or insulating or insulator or oxide) and (dielectric or insulating or insulator or oxide) near5 (metal near2 oxynitride or metal near2 oxy-nitride or metal near3 silicate or metal near3 silicide or hafnium near2 oxynitride or zirconium near2 oxynitride or HfSiON or Hf near2 SiON or ZrSiON or Zr near2 SiON) with silicon with (metal near oxide) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 12:25 |
| - | 7   | gate near3 (dielectric or insulating or insulator or oxide) near6 (metal near2 silicate or hafnium near2 silicate or zirconium near2 silicate or HfSiON or HfSiO or ZrSiON or ZrSiO) near6 (metal adj oxide or TaO or TiO or HfO or ZrO)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 12:29 |
| - | 26  | gate near3 (dielectric or insulating or insulator or oxide) near6 (metal near2 silicate or hafnium near2 silicate or zirconium near2 silicate or HfSiON or HfSiO or ZrSiON or ZrSiO)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 12:41 |
| - | 733 | gate near3 (dielectric or insulating or insulator or oxide) near3 (different or second or nonequal or differing or differ) near4 (material or composition or concentration)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 12:45 |
| - | 388 | gate near2 (dielectric or insulating or insulator or oxide) near3 (different or second or nonequal or differing or differ) near2 (material or composition or concentration)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 12:48 |
| - | 217 | 257/\$.ccls. and (gate near2 (dielectric or insulating or insulator or oxide) near3 (different or second or nonequal or differing or differ) near2 (material or composition or concentration) )   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 13:55 |
| - | 162 | gate near2 (dielectric or oxide or insulator or insulating or insulative) near4 ((metal or metallic or tantalum or titanium or hafnium or zirconium) and silicon and (oxygen or oxide or dioxide))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 14:19 |
| - | 289 | (257/410.ccls. or 257/411.ccls.) and (metal adj oxide or metallic adj oxide or tantalum adj oxide or tungsten adj oxide or titanium adj oxide or zirconium adj oxide or hafnium adj oxide)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 14:21 |
| - | 57  | (257/410.ccls. or 257/411.ccls.) and (metal adj oxide or metallic adj oxide or tantalum adj oxide or tungsten adj oxide or titanium adj oxide or zirconium adj oxide or hafnium adj oxide) near2 (insulator or insulating or insulative or dielectric)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/12 14:24 |